

'842 patent, changes in claim 9 compared to claim 1

19. A semiconductor device, comprising: a substrate of a first doping type at a first doping level having first and second surfaces; a first active region disposed adjacent the first surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof; a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof; transistors formed in at least one of the first active region or second active region; and at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the ~~first~~ surface to the ~~second surface of the~~ substrate.